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Table of Contents

Preface

Chemical-Mechanical Planarization Compatible for Both Copper/Low k Level in a 90 nm Technology and Thick Copper Level in an RF Technology <i>Y. Loquet, C. Perrot, P. Bouillon and B. Iteprat</i>	1
Novel Hybrid Abrasive Particles for Oxide CMP Applications <i>S. R. Mudhivarthi, C. Coutinho, A. Kumar and V. Gupta</i>	9
Effects of CMP Slurry Chemistry on Agglomeration of Alumina and Copper Surface Hardness <i>R. V. Ihnfeldt and J. B. Talbot</i>	21
Analysis of Pre- and Post-Conditioned Polyurethane CMP Pad Surfaces as a Function of Conditioning Temperature <i>A. Prasad, H. Xiang, J. Wang and E. E. Remsen</i>	31
Effect of Slurry Characteristics on the Surface Tribology During Copper CMP Process <i>S. R. Mudhivarthi, V. Kakireddy, A. Kumar and Y. Obeng</i>	45
Composite Polymer Core - Silica Shell Abrasive Particles During Oxide CMP: A Defectivity Study <i>S. Armini, C. M. Whelan and K. Maex</i>	57
Profile Measurements of Microscratches Remaining on Polished Si(001) Wafers <i>T. Shigetoshi, H. Inoue, T. Kawashima, T. Hirokane, T. Kataoka, M. Morita and K. Arima</i>	65
Tuning the Removal Rate of Carbon Doped Oxide during Chemical Mechanical Polishing <i>Z. Liu and J. Bian</i>	73
Integrating a CMP Robust ILD Module <i>J. J. Naughton, J. M. Towner, S. Aytes and M. M. Nelson</i>	81
Author Index	87